

QUERY CONTROL FORM

RTIS USE ONLY

Application No. 09/916 023

Prepared by

Tracking Number 05878493

Examiner-GAU FOURSON-2823

Date _____

Week Date 12/22/23

No. of queries

IFU

JACKET

a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION

- a. Page Missing
- b. Text Continuity
- c. Holes through Data
- d. Other Missing Text
- e. Illegible Text
- f. Duplicate Text
- g. Brief Description
- h. Sequence Listing
- i. Appendix
- j. Amendments
- k. Other

CLAIMS

- a. Claim(s) Missing
- b. Improper Dependency
- c. Duplicate Numbers
- d. Incorrect Numbering
- e. Index Disagrees
- f. Punctuation**
- g. Amendments
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MESSAGE

MESSAGE *Claim 17 now Claim 16 ends with a semi-colon.*

RESPONSE

Changed to period.

Thank you
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wherein removing a second portion of the metal oxide layer is performed in a reaction chamber in the absence of RF activation.

¹³
1415. The method of claim ¹³14, wherein heating the semiconductor substrate is at a temperature between about 625 degrees Celsius to 675 degrees Celsius.

¹³
1516. The method of claim ¹³14, wherein the semiconductor substrate comprises silicon.

¹⁵
¹⁶17. The method of claim ¹⁵16, further comprising:
forming a first interfacial oxide layer under the metal oxide layer;
removing at least a portion of the first interfacial oxide after removing the portion of the metal oxide layer.

¹⁶
1718. (Amended) The method of claim ¹⁶17, wherein removing at least a portion of the first interfacial oxide layer is performed using a species containing hydrogen and fluorine.

¹⁷
1819. The method of claim ¹⁷18, further comprising forming a second interfacial oxide over the semiconductor substrate.

¹⁹21. (Amended) A method of forming a metal oxide comprising:
providing a semiconductor substrate;
forming a metal oxide layer over the semiconductor substrate; and
removing a portion of the metal oxide layer by heating the semiconductor substrate and flowing a gaseous halide;
wherein removing a portion of the metal oxide layer is performed in a reaction chamber in the absence of RF activation.

¹⁹
2022. The method of claim ¹⁹21, wherein the gaseous halide comprises hydrogen.

²⁰
2123. The method of claim ²⁰22, wherein the gaseous halide is HCl.

²⁰
2224. The method of claim ²⁰22, wherein the gaseous halide is HF.

¹⁹
2325. The method of claim ¹⁹21, wherein the metal oxide contains hafnium and oxygen.